



# CHENMKO ENTERPRISE CO.,LTD

## SMALL FLAT NPN Epitaxial Transistor

VOLTAGE 50 Volts CURRENT 2 Ampere

2SC1766PT

Lead free devices

### APPLICATION

\* Power amplifier .

### FEATURE

- \* Small flat package. (SC-62/SOT-89)
- \* Low saturation voltage  $V_{CE(sat)} = -0.5V(\text{max.})(I = -1A)$
- \* High speed switching time:  $t_{stg} = 1.0\mu\text{Sec}(\text{typ.})$
- \*  $PC = 1.0$  to  $2.0W$  (mounted on ceramic substrate).
- \* High saturation current capability.

### CONSTRUCTION

\* NPN Switching Transistor

### MARKING

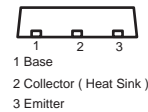
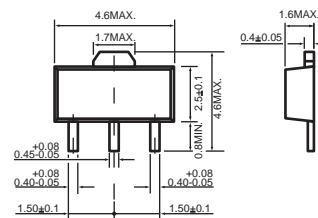
\* hFE Classification P: 1766

Q: Q1766

Y: Y1766



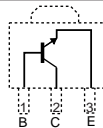
SC-62/SOT-89



Dimensions in millimeters

SC-62/SOT-89

### CIRCUIT



### MAXIMUM RATINGS ( At $T_A = 25^\circ\text{C}$ unless otherwise noted )

RATINGS	CONDITION	SYMBOL	MIN.	MAX.	UNITS
Collector - Base Voltage	Open Emitter	$V_{CB0}$	-	50	Volts
Collector - Emitter Voltage	Open Base	$V_{CE0}$	-	50	Volts
Emitter - Base Voltage	Open Collector	$V_{EB0}$	-	5	Volts
Collector Current DC		$I_C$	-	2	Amps
Peak Collector Current		$I_{CM}$	-	2	Amps
Peak Base Current		$I_{BM}$	-	0.4	Amps
Total Power Dissipation	$T_A \leq 25^\circ\text{C}$ ; Note 1	$P_{TOT}$	-	1000	mW
Storage Temperature		$T_{STG}$	-55	+150	$^\circ\text{C}$
Junction Temperature		$T_J$	-	+150	$^\circ\text{C}$
Operating Ambient Temperature		$T_{AMB}$	-55	+150	$^\circ\text{C}$

### Note

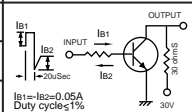
1. Transistor mounted on ceramic substrate  $50\text{mm} \times 50\text{mm} \times 0.8\text{t}$ .
2. Measured at Pulse Width 300  $\mu\text{s}$ , Duty Cycle 2%.

## RATING CHARACTERISTIC CURVES ( 2SC1766PT )

**CHARACTERISTICS** ( At  $T_A = 25^\circ\text{C}$  unless otherwise noted )

PARAMETERS	CONDITION	SYMBOL	MIN.	TYPE	MAX.	UNITS
Collector Cut-off Current	$I_E=0; V_{CB}=50\text{V}$	$I_{CBO}$	-	-	0.1	$\mu\text{A}$
Emitter Cut-off Current	$I_C=0; V_{EB}=5\text{V}$	$I_{CEO}$	-	-	0.1	$\mu\text{A}$
DC Current Gain	$V_{CE}=2\text{V}$ ; Note 1 $I_C=0.5\text{A}$ ; Note 2 $I_C=2.0\text{A}$	$h_{FE}$	70 20	- -	390 -	
Collector-Emitter Saturation Voltage	$I_C=1\text{A}; I_B=0.05\text{A}$	$V_{CEsat}$	-	-	0.5	Volts
Base-Emitter Saturation Voltage	$I_C=1\text{A}; I_B=0.05\text{A}$	$V_{BEsat}$	-	-	1.2	mVolts
Collector Capacitance	$I_E=I_C=0; V_{CB}=-10\text{V}$ ; $f=1\text{MHz}$	$C_C$	-	40	-	$\text{pF}$
Transition Frequency	$I_C=0.5\text{A}; V_{CE}=2\text{V}$ ; $f=100\text{MHz}$	$f_T$	-	120	-	$\text{MHz}$

**SWITCHING TIMES** ( Between 10% and 90% levels )

PARAMETERS	CONDITION	SYMBOL	MIN.	TYPE	MAX.	UNITS
Turn-on Time		$t_{on}$	-	0.1	-	$\mu\text{Sec}$
Storage Time		$t_s$	-	1.0	-	$\mu\text{Sec}$
Fall Time		$t_f$	-	0.1	-	$\mu\text{Sec}$

**Note :**

1. Pulse test:  $t_p \leq 300\mu\text{Sec}$ ;  $\delta \leq 0.02$ .
2.  $h_{FE}(1)$  Classification P:82 to 180 Q: 120 to 270, Y: 180 to 390

# RATING CHARACTERISTIC CURVES ( 2SC1766PT )

## Typical Electrical Characteristics

Figure 1.  $V_{CE} - I_C$

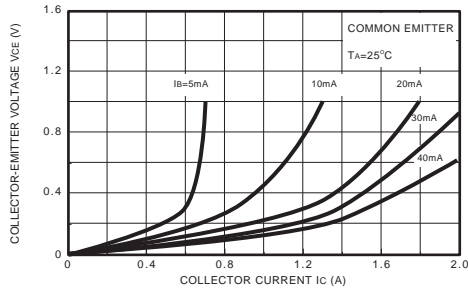


Figure 2.  $V_{CE} - I_C$

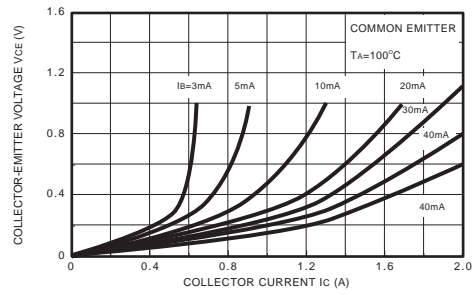


Figure 3.  $V_{CE} - I_C$

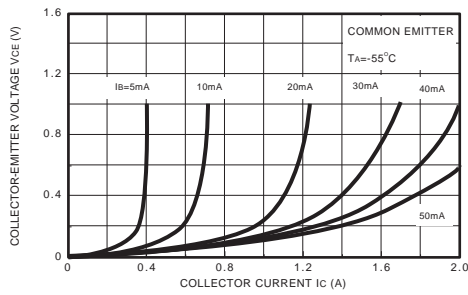


Figure 4.  $h_{FE} - I_C$

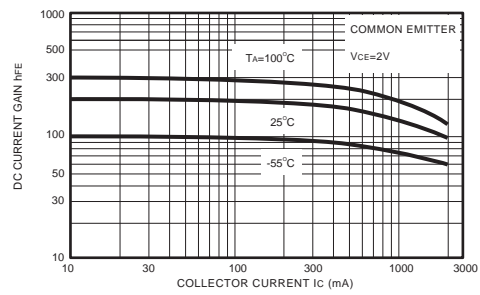


Figure 5.  $V_{CE(sat)} - I_C$

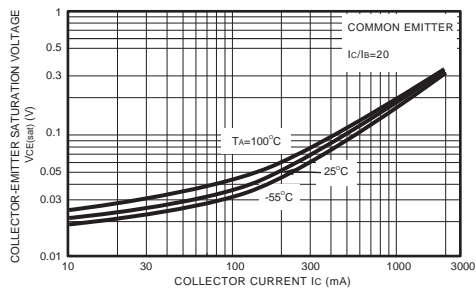
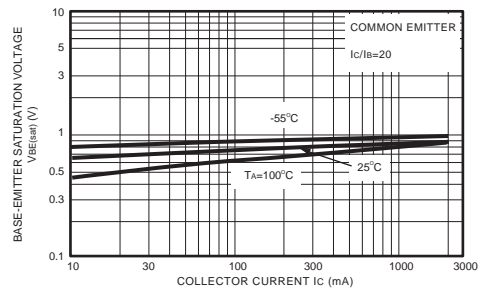


Figure 6.  $V_{BE(sat)} - I_C$



# RATING CHARACTERISTIC CURVES ( 2SC1766PT )

## Typical Electrical Characteristics

Figure 7.  $I_c - V_{BE}$

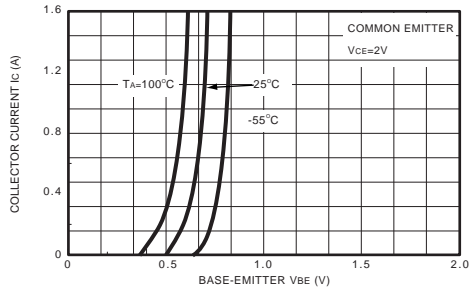


Figure 8.  $P_c - T_A$

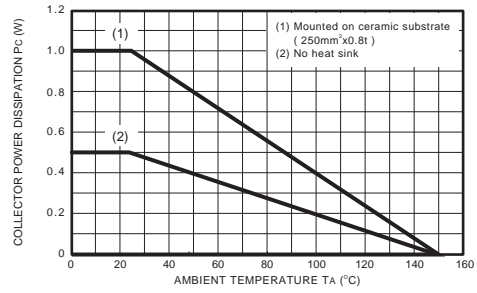


Figure 9. Safe Operation Area

